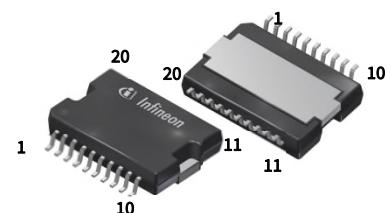


IGO60R070D1

600V CoolGaN™ enhancement-mode Power Transistor

Features

- Enhancement mode transistor – Normally OFF switch
- Ultra fast switching
- No reverse-recovery charge
- Capable of reverse conduction
- Low gate charge, low output charge
- Superior commutation ruggedness
- Qualified for industrial applications according to JEDEC Standards (JESD47 and JESD22)



Benefits

- Improves system efficiency
- Improves power density
- Enables higher operating frequency
- System cost reduction savings
- Reduces EMI

Gate	9, 10
Drain	13,14,15,16,17,18
Kelvin Source	8
Source	1,2,3,4,5,6,7, heatslug
not connected	11,12,19,20

Applications

Industrial, telecom, datacenter SMPS based on the half-bridge topology (half-bridge topologies for hard and soft switching such as Totem pole PFC, high frequency LLC).

For other applications: review CoolGaN™ reliability white paper and contact Infineon regional support

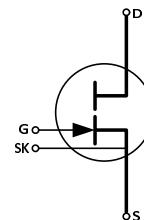


Table 1 Key Performance Parameters at $T_j = 25^\circ\text{C}$

Parameter	Value	Unit
$V_{DS,\max}$	600	V
$R_{DS(\text{on}),\max}$	70	mΩ
$Q_{G,\text{typ}}$	5.8	nC
$I_{D,\text{pulse}}$	60	A
$Q_{oss} @ 400 \text{ V}$	41	nC
Q_{rr}	0	nC



Table 2 Ordering Information

Type / Ordering Code	Package	Marking	Related links
IGO60R070D1	PG-DSO-20-85	60R070D1	see Appendix A

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified.

Continuous application of maximum ratings can deteriorate transistor lifetime. For further information, contact your local Infineon sales office.

Table 3 Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Drain Source Voltage ¹	$V_{DS,\max}$	-	-	600	V	$V_{GS} = 0\text{ V}$
Continuous current, drain source	I_D	-	-	31	A	$T_c = 25^\circ\text{C}; T_j = T_{j,\max}$
		-	-	20		$T_c = 100^\circ\text{C}; T_j = T_{j,\max}$
		-	-	14		$T_c = 125^\circ\text{C}; T_j = T_{j,\max}$
Pulsed current, drain source ²³	$I_{D,\text{pulse}}$	-	-	60	A	$T_c = 25^\circ\text{C}; I_G = 26.1\text{ mA};$ See Figure 3;Figure 5;
Pulsed current, drain source ³⁴	$I_{D,\text{pulse}}$	-	-	35	A	$T_c = 125^\circ\text{C}; I_G = 26.1\text{ mA};$ See Figure 4;Figure 6;
Gate current, continuous ³⁴⁵	$I_{G,\text{avg}}$	-	-	20	mA	$T_j = -55^\circ\text{C} \text{ to } 150^\circ\text{C};$
Gate current, pulsed ³⁵	$I_{G,\text{pulse}}$	-	-	2000	mA	$T_j = -55^\circ\text{C} \text{ to } 150^\circ\text{C};$ $t_{PULSE} = 50\text{ ns}, f=100\text{ kHz}$
Gate source voltage, continuous ⁵	V_{GS}	-10	-	-	V	$T_j = -55^\circ\text{C} \text{ to } 150^\circ\text{C};$
Gate source voltage, pulsed ⁵	$V_{GS,\text{pulse}}$	-25	-	-	V	$T_j = -55^\circ\text{C} \text{ to } 150^\circ\text{C};$ $t_{PULSE} = 50\text{ ns}, f = 100\text{ kHz};$ open drain
Power dissipation	P_{tot}	-	-	125	W	$T_c = 25^\circ\text{C}$
Operating temperature	T_j	-55	-	150	°C	
Storage temperature	T_{stg}	-55	-	150	°C	Max shelf life depends on storage conditions.
Drain-source voltage slew-rate	dV/dt			200	V/ns	

¹ All devices are 100% tested at $I_{DS} = 12.2\text{ mA}$ to assure $V_{DS} \geq 800\text{ V}$

² Limits derived from product characterization, parameter not measured during production

³ Ensure that average gate drive current, $I_{G,\text{avg}}$ is $\leq 20\text{ mA}$. Please see figure 27 for $I_{G,\text{avg}}$, $I_{G,\text{pulse}}$ and I_G details

⁴ Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

⁵ We recommend using an advanced driving technique to optimize the device performance. Please see gate drive application note for details.

2 Thermal characteristics

Table 4 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	R_{thJC}	-	-	1	°C/W	
Reflow soldering temperature	T_{sold}	-	-	245	°C	MSL3

3 Electrical characteristics

at $T_j = 25^\circ\text{C}$, unless specified otherwise

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate threshold voltage	$V_{GS(\text{th})}$	0.9	1.2	1.6	V	$I_{DS} = 2.6 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 25^\circ\text{C}$
		0.7	1.0	1.4		$I_{DS} = 2.6 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 125^\circ\text{C}$
Drain-Source leakage current	I_{DSS}	-	1	100	μA	$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$
		-	20	-		$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150^\circ\text{C}$
Drain-Source leakage current at application conditions ¹	$I_{DSS\text{app}}$	-	60	-	μA	$V_{DS} = 400 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125^\circ\text{C}$
Gate-Source leakage current	I_{GSS}	-1	-	-	mA	$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25^\circ\text{C}$
		-1	-	-		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 125^\circ\text{C}$
Drain-Source on-state resistance	$R_{DS(\text{on})}$	-	0.055	0.070	Ω	$I_G = 26.1 \text{ mA}; I_D = 8 \text{ A}; T_j = 25^\circ\text{C}$
		-	0.100	-		$I_G = 26.1 \text{ mA}; I_D = 8 \text{ A}; T_j = 150^\circ\text{C}$
Gate resistance	$R_{G,\text{int}}$	-	0.78	-	Ω	LCR impedance measurement; $f = f_{\text{res}}$; open drain;

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	380	-	pF	$V_{GS} = 0 \text{ V}; V_{DS} = 400 \text{ V}; f = 1 \text{ MHz}$
Output capacitance	C_{oss}	-	72	-	pF	$V_{GS} = 0 \text{ V}; V_{DS} = 400 \text{ V}; f = 1 \text{ MHz}$
Reverse Transfer capacitance	C_{rss}	-	0.3	-	pF	$V_{GS} = 0 \text{ V}; V_{DS} = 400 \text{ V}; f = 1 \text{ MHz}$
Effective output capacitance, energy related ²	$C_{o(er)}$	-	80	-	pF	$V_{DS} = 0 \text{ to } 400 \text{ V}$
Effective output capacitance, time related ³	$C_{o(tr)}$	-	102.5	-	pF	$V_{GS} = 0 \text{ V}; V_{DS} = 0 \text{ to } 400 \text{ V}; I_D = \text{const}$
Output charge	Q_{oss}	-	41	-	nC	$V_{DS} = 0 \text{ to } 400 \text{ V}$
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	see Figure 23
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	see Figure 23
Rise time	t_r	-	9	-	ns	see Figure 23
Fall time	t_f	-	13	-	ns	see Figure 23

¹ Parameter represents end of use leakage in applications

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V

³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate charge	Q_G	-	5.8	-	nC	$I_{GS} = 0$ to 10 mA; $V_{DS} = 400$ V; $I_D = 8$ A

Table 8 Reverse conduction characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Source-Drain reverse voltage	V_{SD}	-	2.2	2.5	V	$V_{GS} = 0$ V; $I_{SD} = 8$ A
Pulsed current, reverse	$I_{S,pulse}$	-	-	60	A	$I_G = 26.1$ mA
Reverse recovery charge	Q_{rr}^1	-	0	-	nC	$I_S = 8$ A, $V_{DS} = 400$ V
Reverse recovery time	t_{rr}	-	0	-	ns	
Peak reverse recovery current	I_{rrm}	-	0	-	A	

¹ Excluding Qoss

4 Electrical characteristics diagrams

at $T_j = 25^\circ\text{C}$, unless specified otherwise

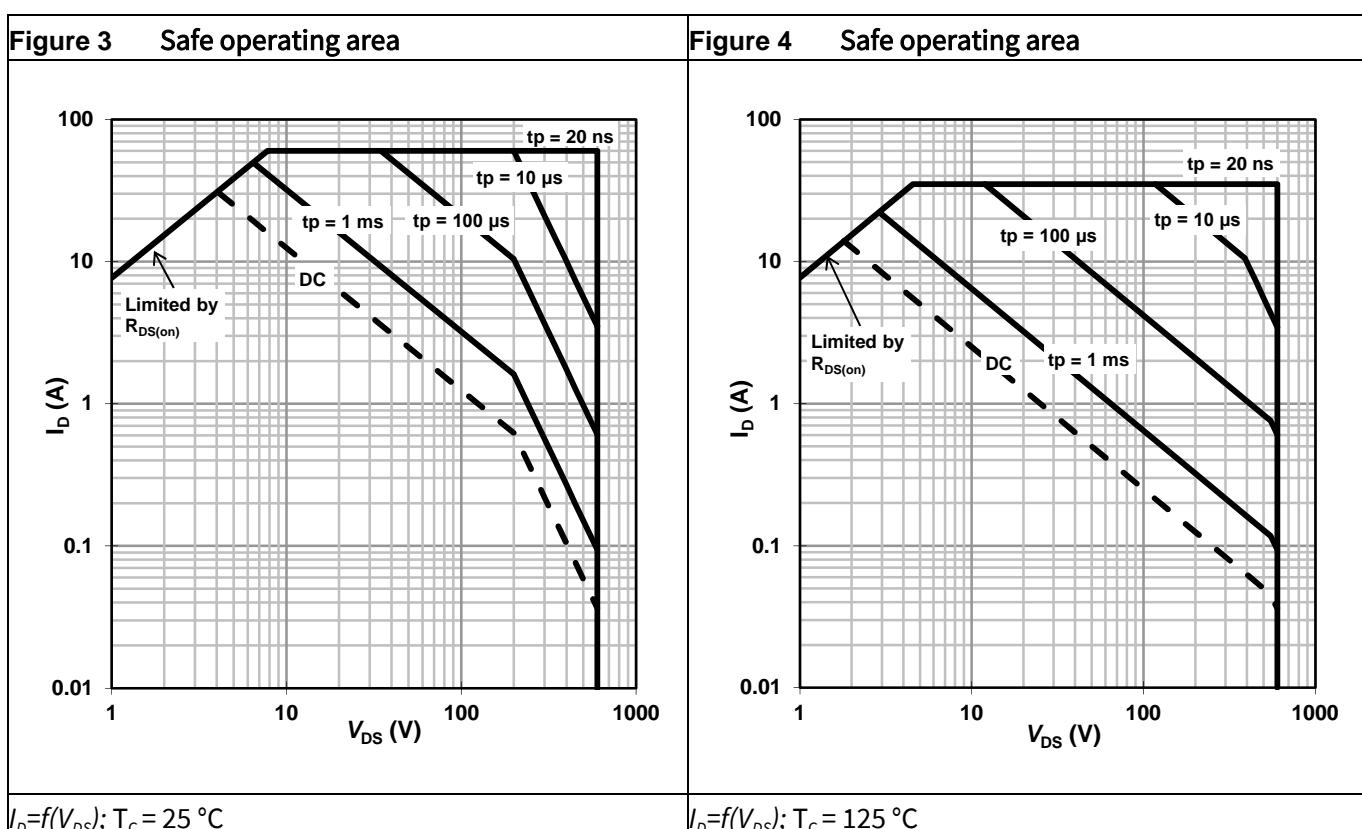
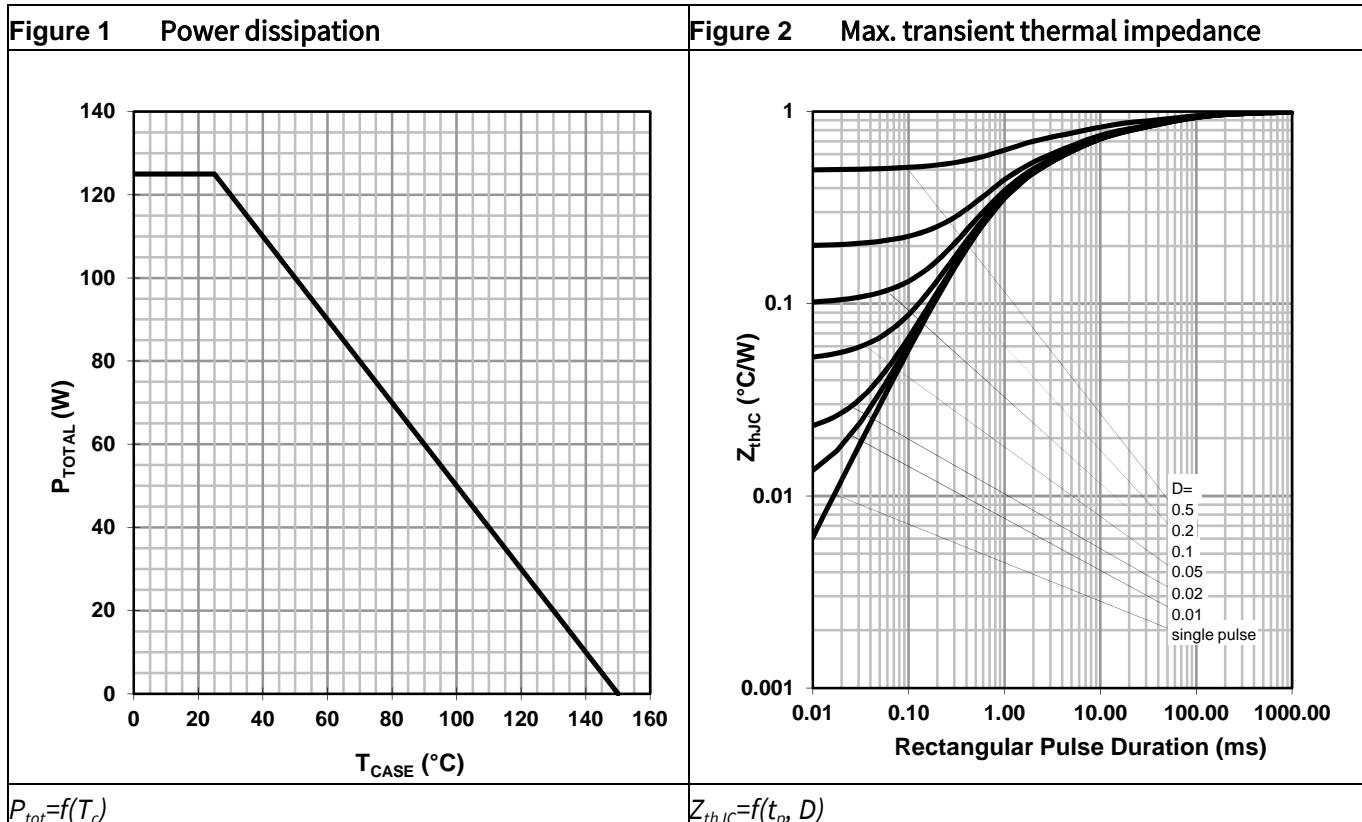


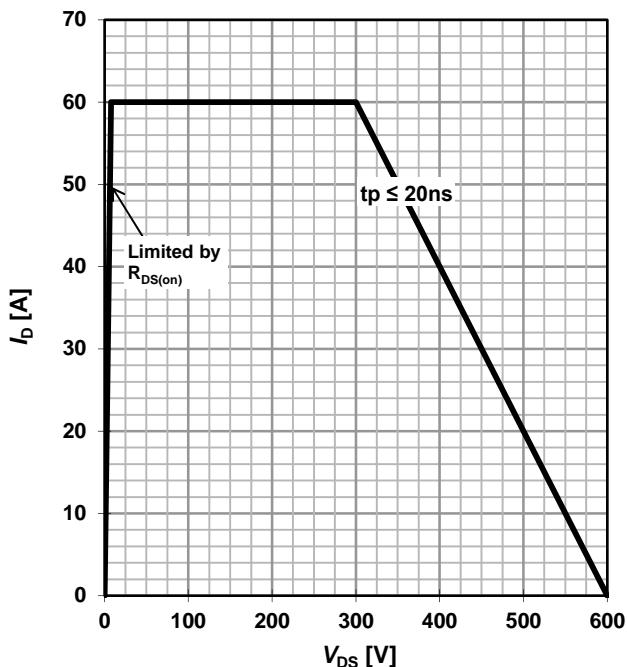
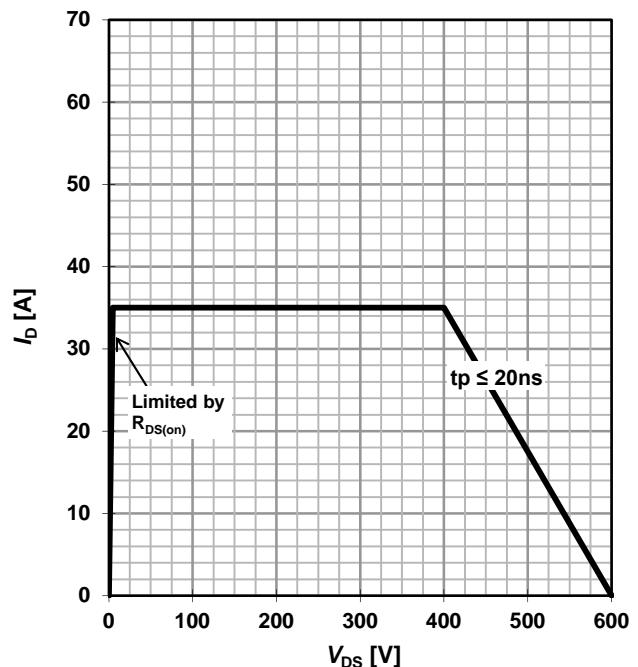
Figure 5 Repetitive safe operating area¹ $T_c = 25 \text{ }^\circ\text{C}; T_j \leq 150 \text{ }^\circ\text{C}$ Figure 6 Repetitive safe operating area¹ $T_c = 125 \text{ }^\circ\text{C}; T_j \leq 150 \text{ }^\circ\text{C}$

Figure 7 Typ. output characteristics

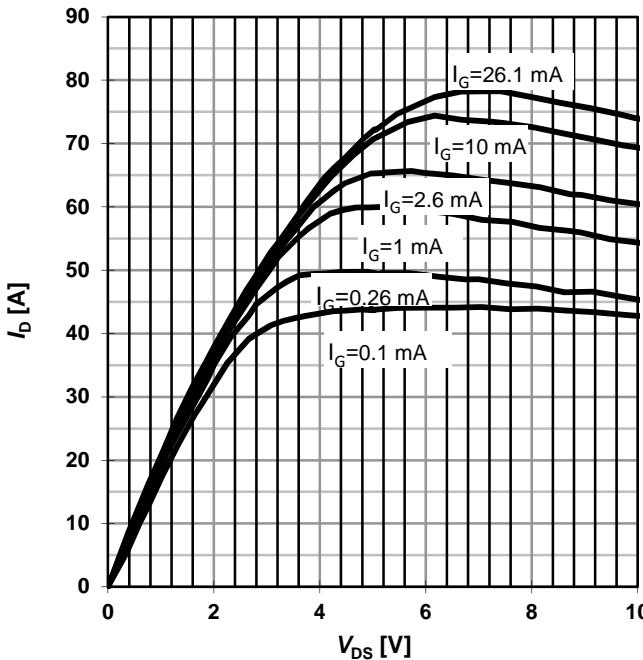
 $I_D = f(V_{DS}, I_G); T_j = 25 \text{ }^\circ\text{C}$

Figure 8 Typ. output characteristics

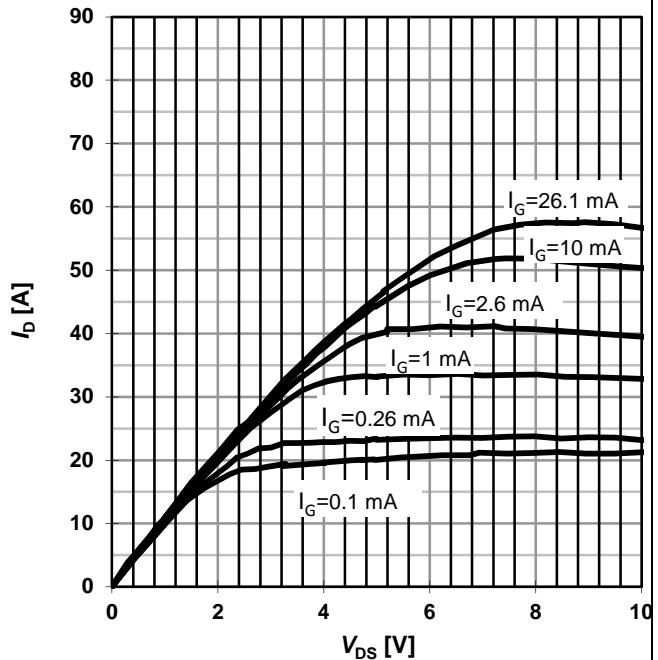
 $I_D = f(V_{DS}, I_G); T_j = 125 \text{ }^\circ\text{C}$ ¹ Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

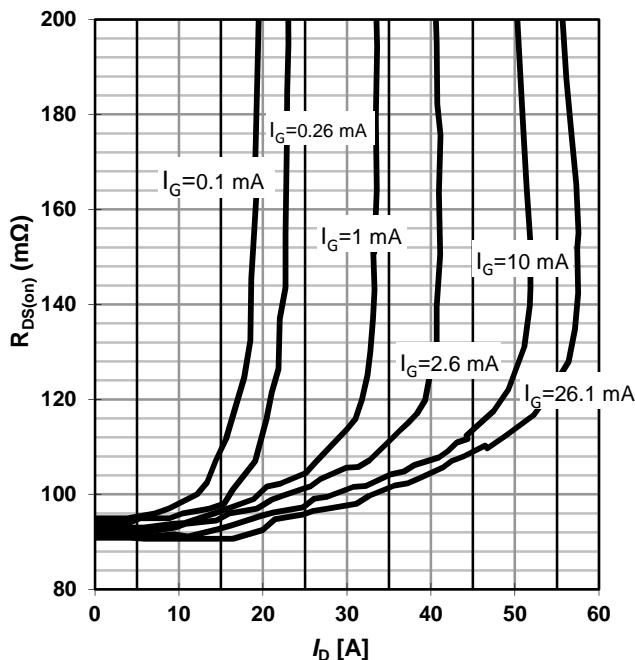
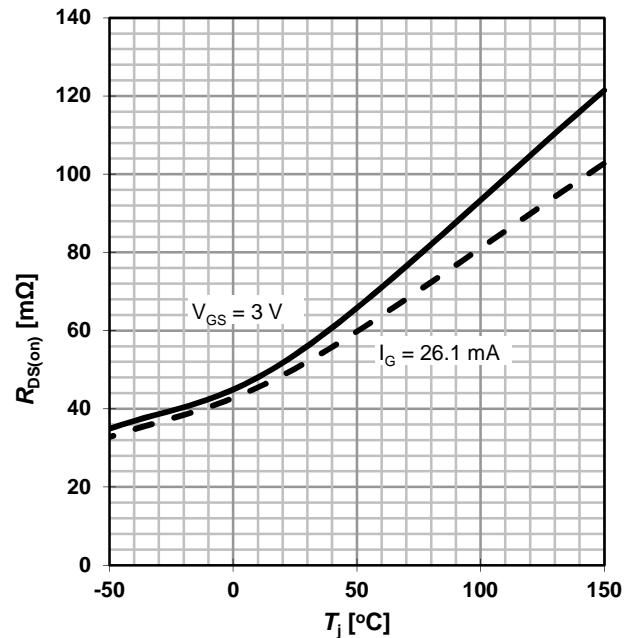
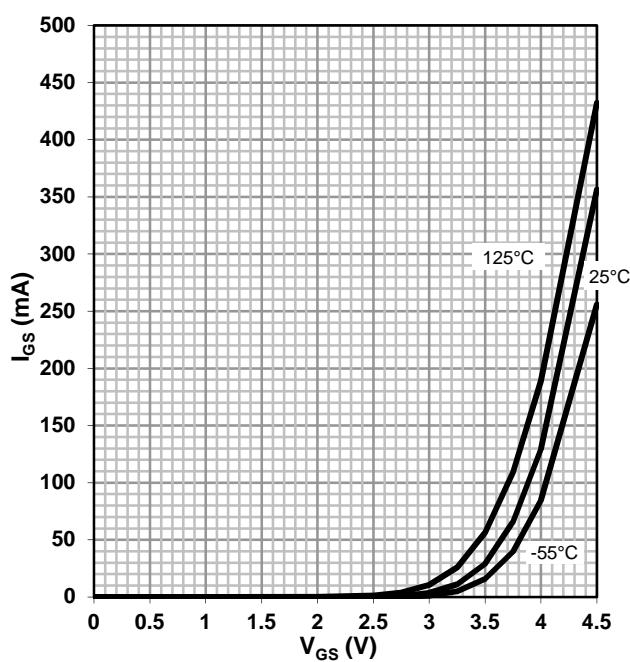
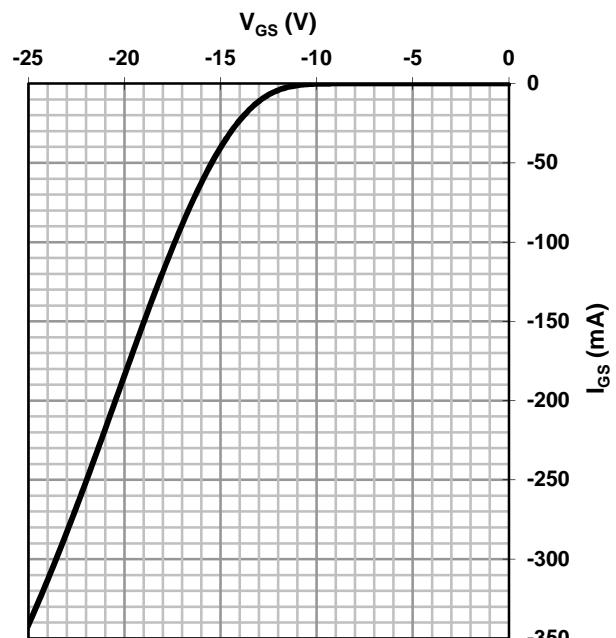
Figure 9 Typ. Drain-source on-state resistance
 $R_{DS(on)}=f(I_D, I_G); T_j = 125\text{ }^\circ\text{C}$
Figure 10 Drain-source on-state resistance
 $R_{DS(on)}=f(T_j); I_D = 8\text{ A}$
Figure 11 Typ. gate characteristics forward
 $I_{GS}=f(V_{GS}, T_j); \text{open drain}$
Figure 12 Typ. gate characteristics reverse
 $I_{GS}=f(V_{GS}); T_j = 25\text{ }^\circ\text{C}$

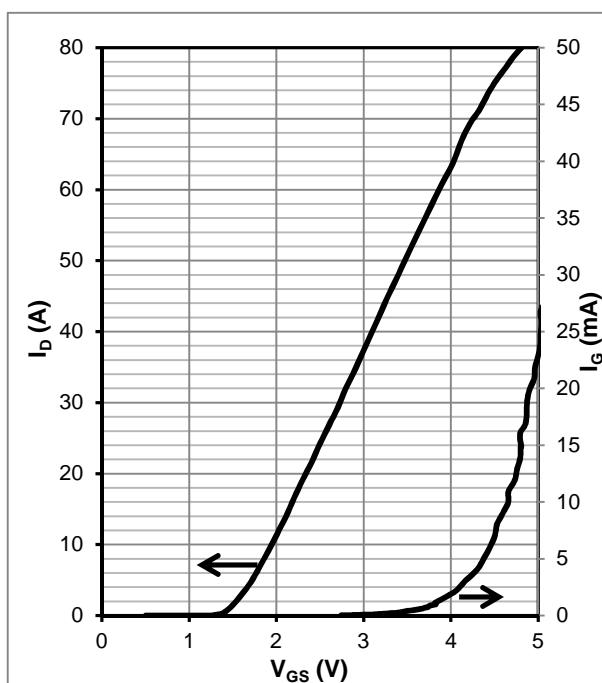
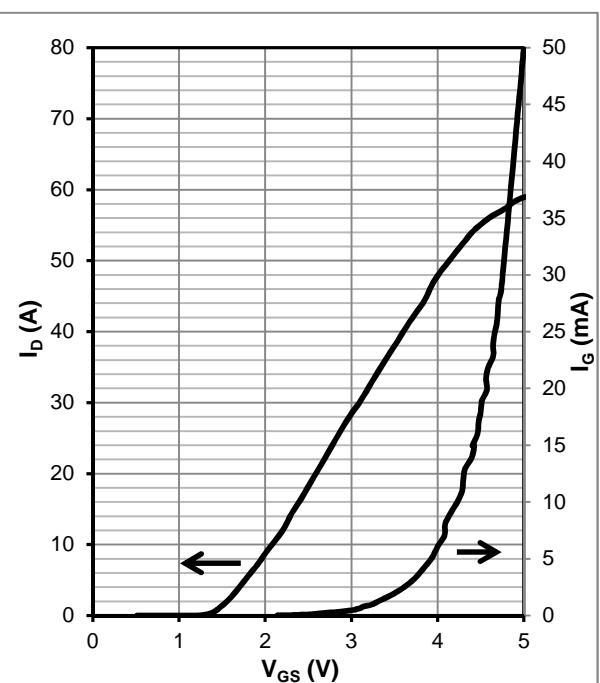
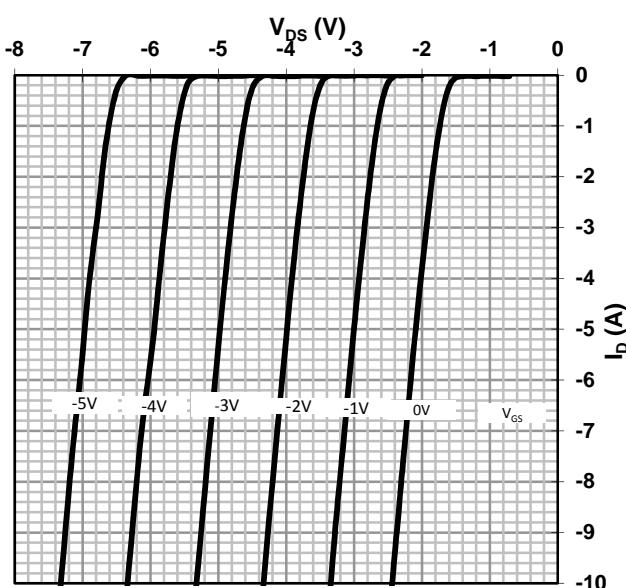
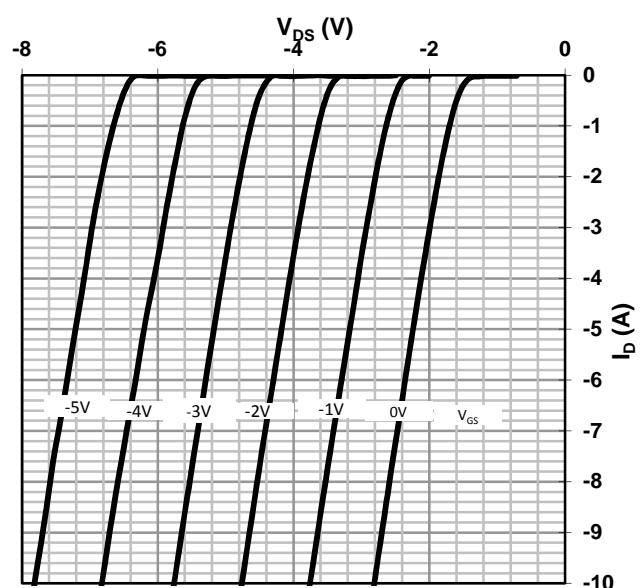
Figure 13 Typ. transfer characteristics
 $I_D, I_G = f(V_{GS}); V_{DS} = 8 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$
Figure 14 Typ. transfer characteristics
 $I_D, I_G = f(V_{GS}); V_{DS} = 8 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$
Figure 15 Typ. channel reverse characteristics
 $V_{DS} = f(I_D, V_{GS}); T_j = 25 \text{ }^\circ\text{C}$
Figure 16 Typ. channel reverse characteristics
 $V_{DS} = f(I_D, V_{GS}); T_j = 125 \text{ }^\circ\text{C}$

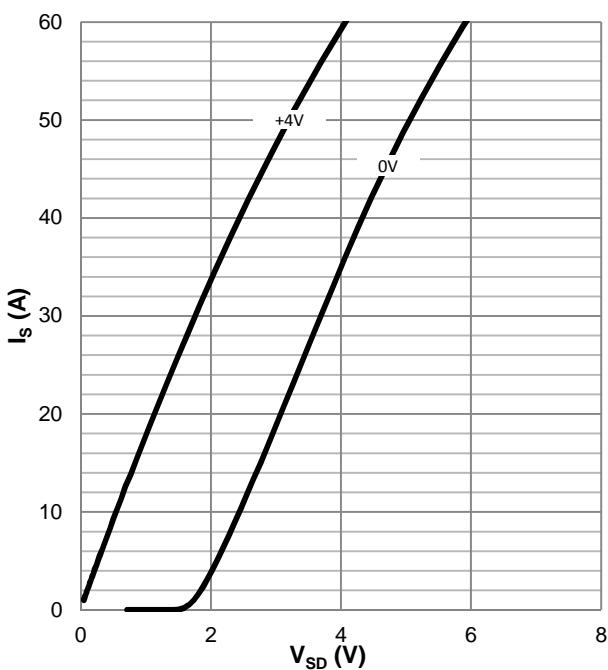
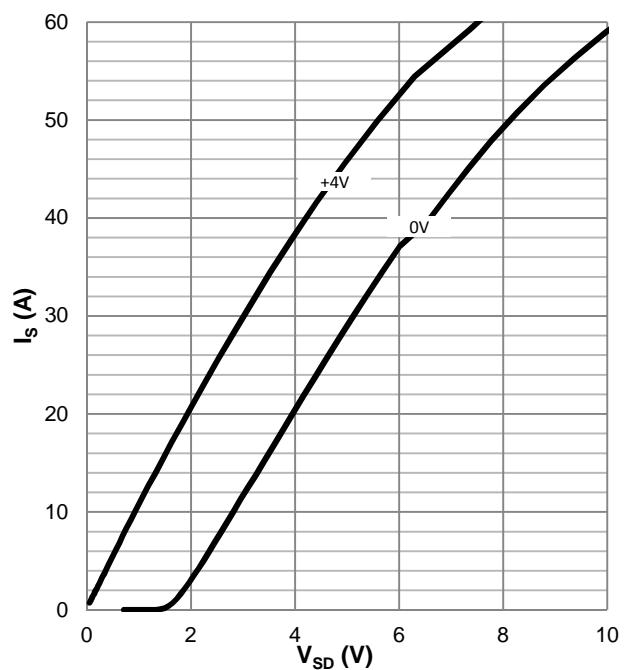
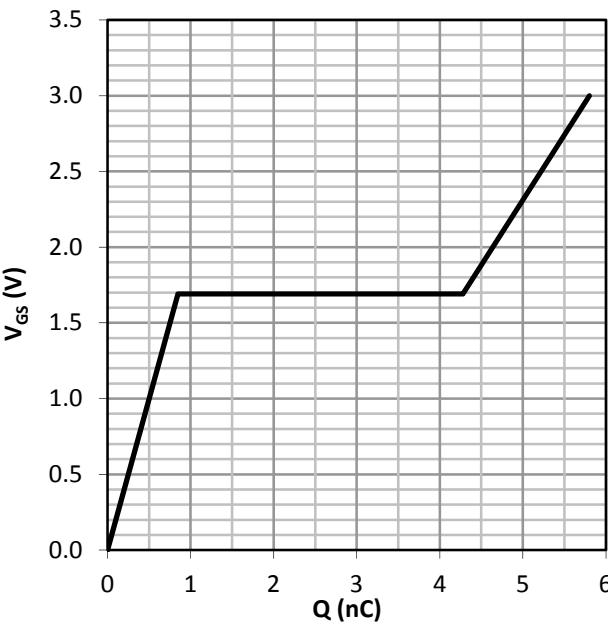
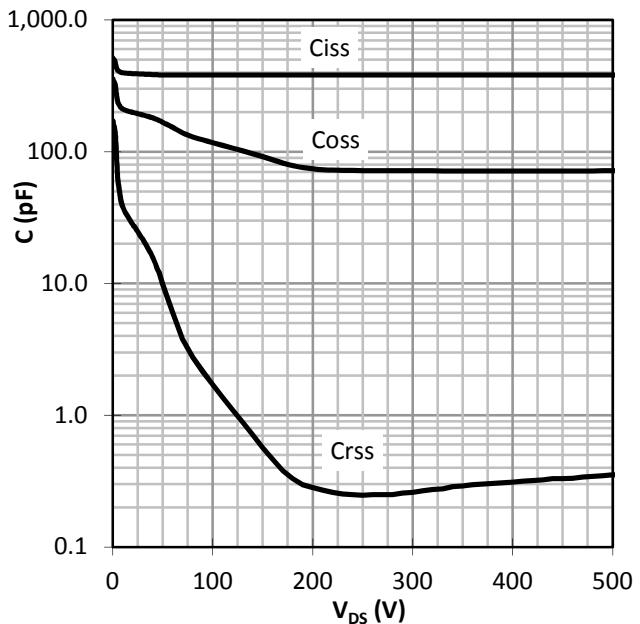
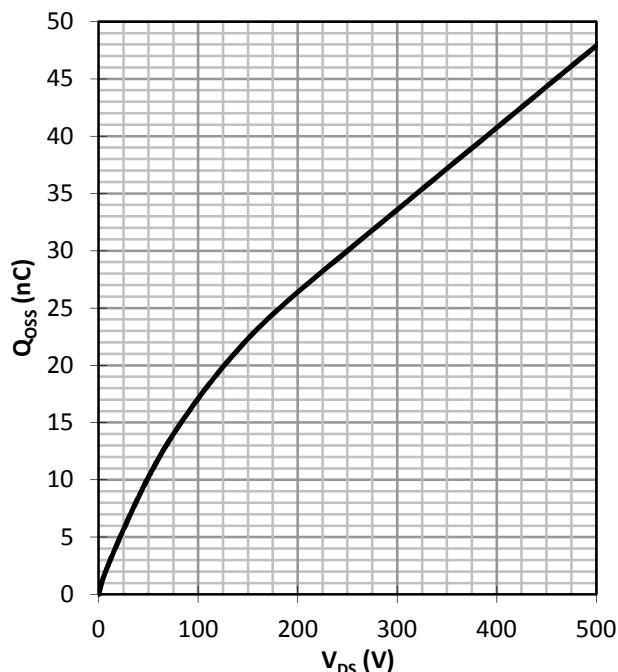
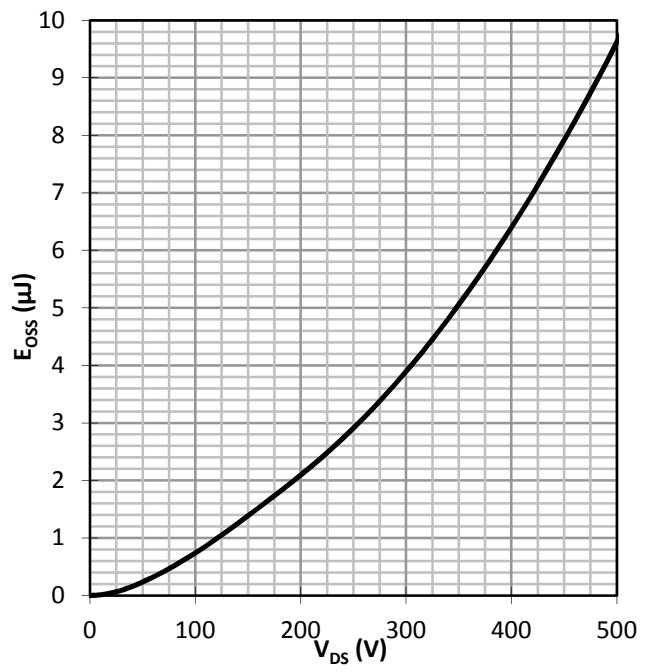
Figure 17 Typ. channel reverse characteristics
 $I_D = f(V_{DS}, V_{GS})$; $T_j = 25^\circ\text{C}$
Figure 18 Typ. channel reverse characteristics
 $I_D = f(V_{DS}, V_{GS})$; $T_j = 125^\circ\text{C}$
Figure 19 Typ. gate charge
 $V_{GS} = f(Q_G)$; $V_{DCLINK} = 400\text{ V}$; $I_D = 8\text{ A}$
Figure 20 Typ. capacitances
 $C_{xSS} = f(V_{DS})$

Figure 21 Typ. output charge

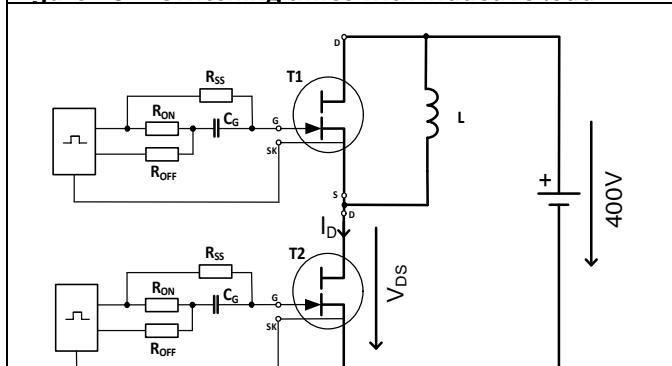
$$Q_{OSS} = f(V_{DS})$$

Figure 22 Typ. Coss stored Energy

$$E_{OSS} = f(V_{DS})$$

5 Test Circuits

Figure 23 Switching times with inductive load



$I_D = 8A$, $R_{ON} = 10 \Omega$; $R_{OFF} = 10 \Omega$; $R_{SS} = 820 \Omega$; $C_G = 2 \text{ nF}$;
 $V_{DRV} = 12V$

Figure 24 Switching times waveform

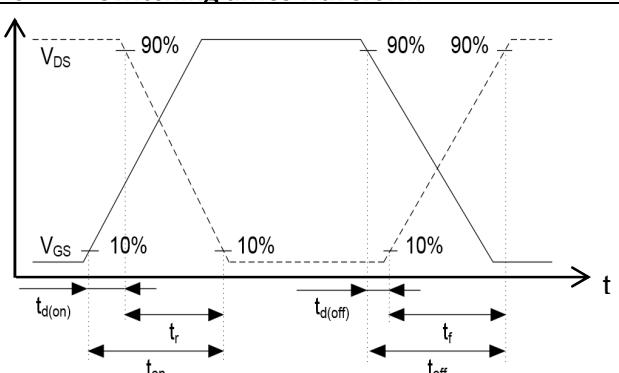
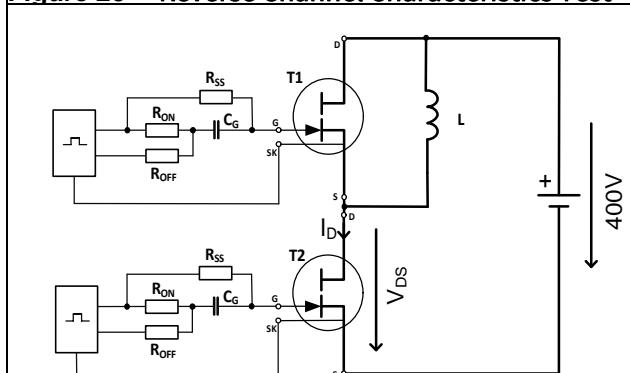
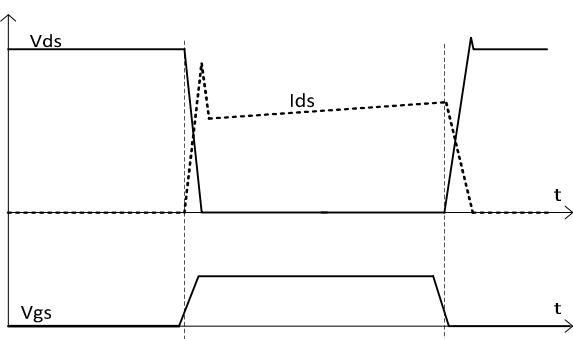


Figure 25 Reverse Channel Characteristics Test



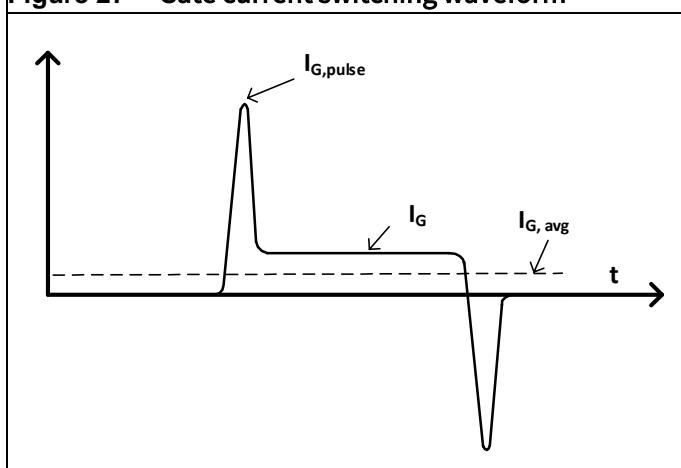
$I_D = 8A$, $R_{ON} = 10 \Omega$; $R_{OFF} = 10 \Omega$; $R_{SS} = 820 \Omega$; $C_G = 2 \text{ nF}$;
 $V_{DRV} = 12V$

Figure 26 Typical Reverse Channel Recovery



The recovery charge is Q_{oss} only, no additional Q_{rr}

Figure 27 Gate current switching waveform



6 Package Outlines

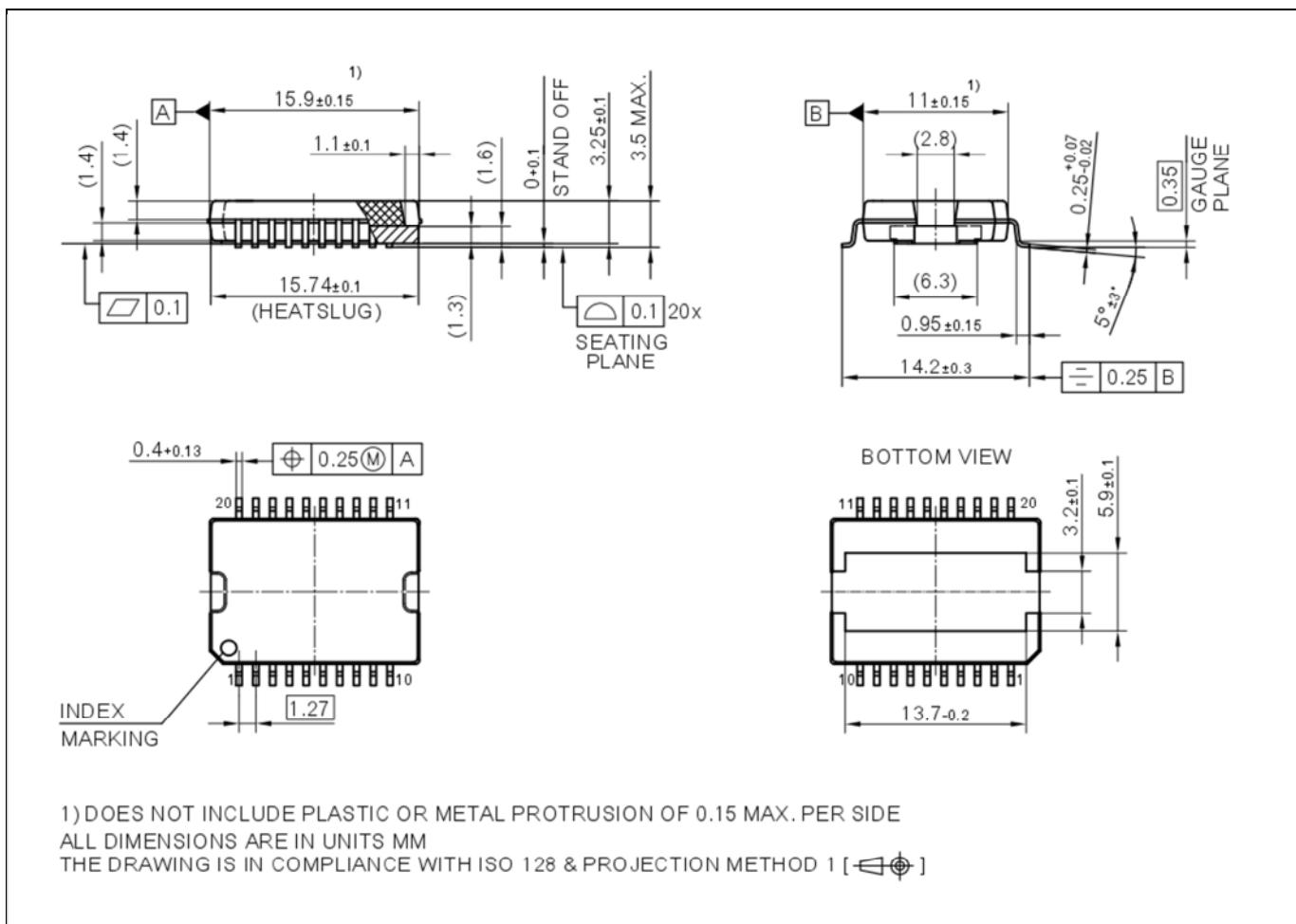


Figure 28 PG-DSO-20-85 Package Outline, dimensions (mm)

7 Appendix A

Table 9 Related links

- IFX CoolGaN™ webpage: www.infineon.com/why-coolgan
- IFX CoolGaN™ reliability white paper: www.infineon.com/gan-reliability
- IFX CoolGaN™ gate drive application note: www.infineon.com/driving-coolgan
- IFX CoolGaN™ applications information:
 - www.infineon.com/gan-in-server-telecom
 - www.infineon.com/gan-in-wirelesscharging
 - www.infineon.com/gan-in-audio
 - www.infineon.com/gan-in-adapter-charger

8 Revision History

Major changes since the last revision

Revision	Date	Description of change
2.0	2018-04-24	Final version release
2.1	2018-10-12	Updated application section; added Appendix A and Fig. 27; updated maximum rating table footnotes, switching times and figures.

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Электрон
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